Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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HAT2173N

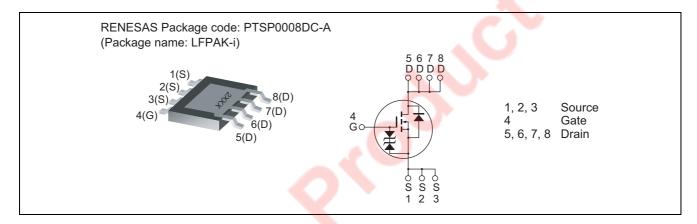
Silicon N Channel Power MOS FET Power Switching

REJ03G1684-0100 Rev.1.00 May 28, 2008

Features

- Capable of 8 V gate drive
- Low drive current
- High density mounting
- Low on-resistance $R_{DS(on)} = 12.3 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	25	Α
Drain peak current	I _{D(pulse)} Note1	100	Α
Body-drain diode reverse drain current	I _{DR}	25	Α
Avalanche current	I _{AP} Note 2	25	Α
Avalanche energy	E _{AR} Note 2	62.5	mJ
Channel dissipation	Pch Note3	30	W
Channel to case thermal resistance	θch-C	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tch = 25°C, Rg \geq 50 Ω

3. $Tc = 25^{\circ}C$

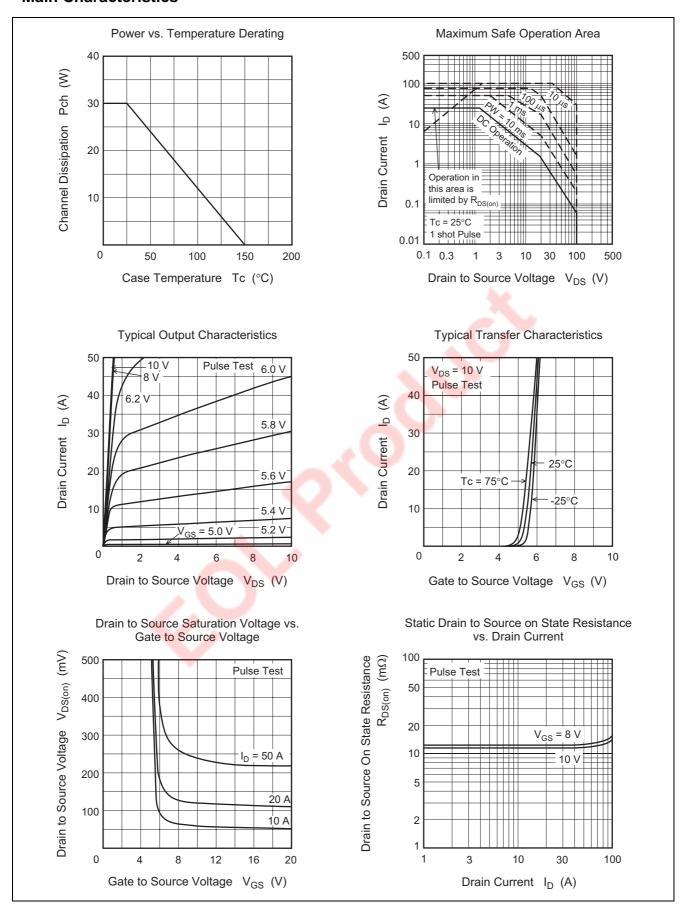
Electrical Characteristics

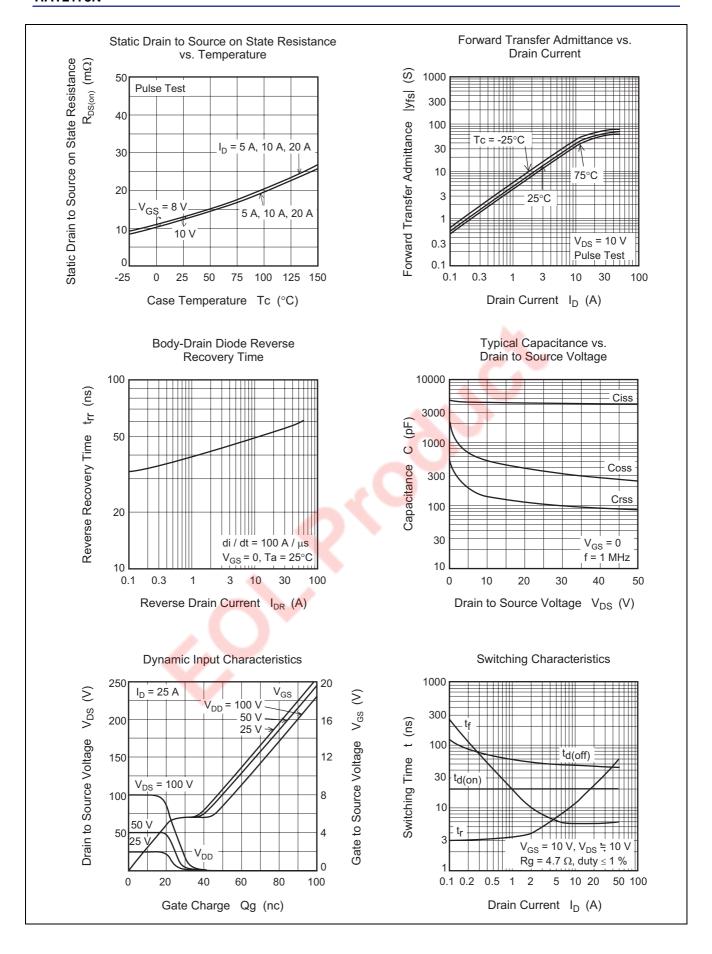
 $(Ta = 25^{\circ}C)$

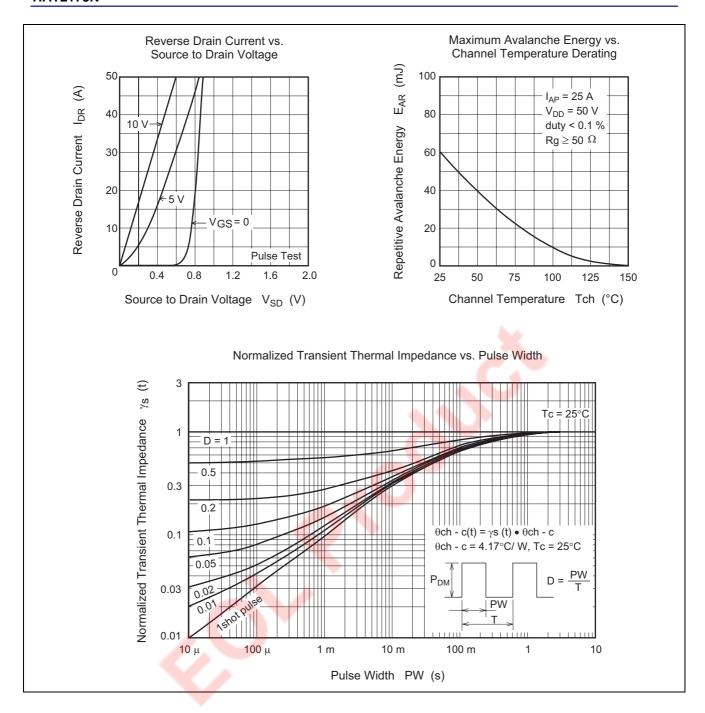
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 40 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	4.0	_	6.0	V	$V_{DS} = 10 \text{ V}, I_D = 20\text{mA}$
Static drain to source on state	R _{DS(on)}	_	12.3	15.3	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	13.3	17.8	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 8 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	27	45	_	S	$I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	4350	_	рF	$V_{DS} = 10 \ V, V_{GS} = 0,$
Output capacitance	Coss	_	520	_	рF	f = 1 MHz
Reverse transfer capacitance	Crss	_	150	_	рF	
Gate resistance	Rg	_	0.5	_	Ω	
Total gate charge	Qg	_	61	_	nC	$V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V},$
Gate to source charge	Qgs	_	23	_	nC	$I_D = 25 A$
Gate to drain charge	Qgd	_	14.5	_	nC	
Turn-on delay time	t _{d(on)}	_	20	_	ns	$V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A},$
Rise time	t _r	_	15	_	ns	$V_{DD} \cong 30 \text{ V}, R_L = 2.4 \Omega,$
Turn-off delay time	t _{d(off)}	_	37		ns	$Rg = 4.7 \Omega$
Fall time	t _f	_	5.7	-	ns	
Body-drain diode forward voltage	V_{DF}	_	0.82	1.07	V	$I_F = 25 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery	t _{rr}	_	55		ns	$I_F = 25 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 100 A/ \mu s$

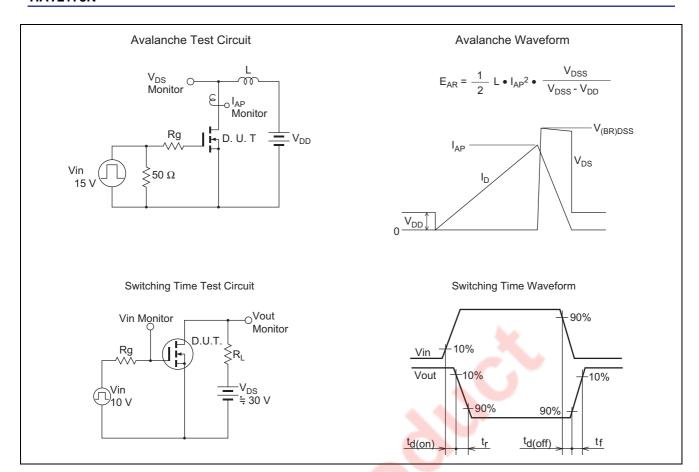
Notes: 4. Pulse test

Main Characteristics

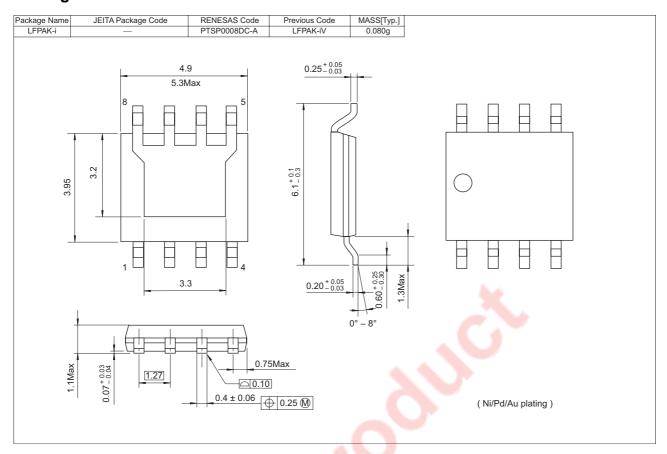








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2173N-EL-E	2500 pcs	Taping

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